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(71) **Applicant (for all designated States except US):** **MICRON TECHNOLOGY, INC.** [US/US]; Mail Stop 525, 8000 South Federal Way, Boise, ID 83707-0006 (US).

(72) **Inventors; and**

(75) **Inventors/Applicants (for US only):** **LIU, Jun** [US/US]; 924 Pennfield Place, Caldwell, ID 83605 (US). **VIOLETTE, Michael, P.** [US/US]; 1088 East Fleetwood Court, Boise, ID 83706 (US).

(74) **Agents:** **BARRETT, Tyler, J.** et al.; Traskbritt, 230 South 500 East, Suite 300, P. O. Box 2550, Salt Lake City, UT 84110-2550 (US).

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- (54) Title:** MEMORY DEVICES HAVING ELECTRODES COMPRISING NANOWIRES, SYSTEMS INCLUDING SAME AND METHODS OF FORMING SAME

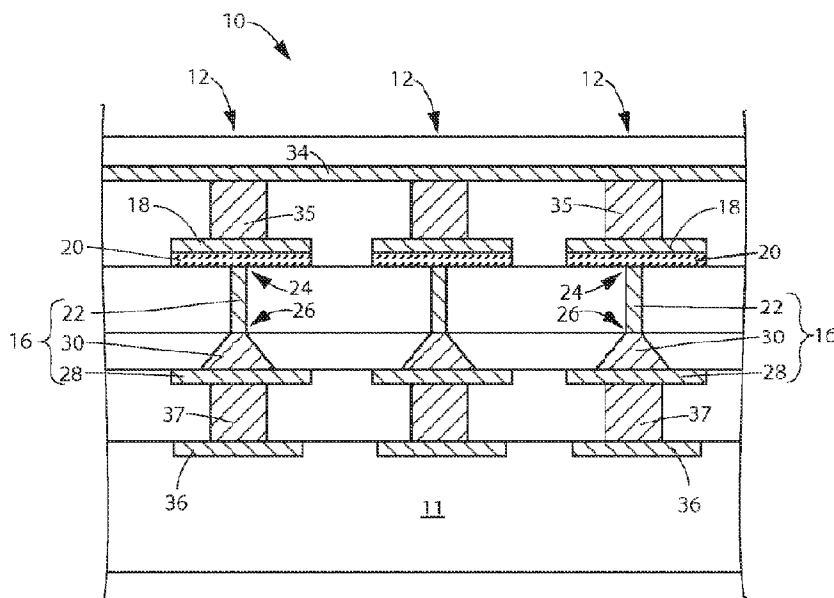


FIG. 1A

- (57) Abstract:** Memory devices having memory cells comprising variable resistance material include an electrode comprising a single nanowire. Various methods may be used to form such memory devices, and such methods may comprise establishing contact between one end of a single nanowire and a volume of variable resistance material in a memory cell. Electronic systems include such memory devices.



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